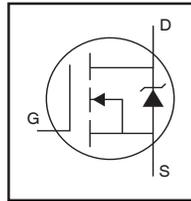


Features

- Advanced Planar Technology
- Low On-Resistance
- Logic Level Gate Drive
- Dynamic dv/dt Rating
- 150°C Operating Temperature
- Fast Switching
- Fully Avalanche Rated
- Repetitive Avalanche Allowed up to Tjmax
- Lead-Free, RoHS Compliant
- Automotive Qualified*

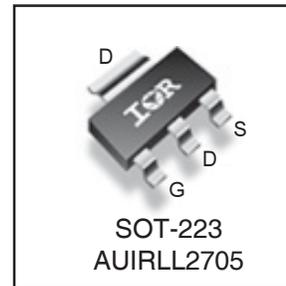
HEXFET® Power MOSFET



$V_{(BR)DSS}$	55V
$R_{DS(on)}$ max.	0.04Ω
I_D	3.8A

Description

Specifically designed for Automotive applications, this cellular design of HEXFET® Power MOSFETs utilizes the latest processing techniques to achieve low on-resistance per silicon area. This benefit combined with the fast switching speed and ruggedized device design that HEXFET power MOSFETs are well known for, provides the designer with an extremely efficient and reliable device for use in Automotive and a wide variety of other applications.



G	D	S
Gate	Drain	Source

Base Part Number	Package Type	Standard Pack		Orderable Part Number
		Form	Quantity	
AUIRLL2705	SOT-223	Tube	95	AUIRLL2705
		Tape and Reel	2500	AUIRLL2705TR

Absolute Maximum Ratings

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only; and functional operation of the device at these or any other condition beyond those indicated in the specifications is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability. The thermal resistance and power dissipation ratings are measured under board mounted and still air conditions. Ambient temperature (T_A) is 25°C, unless otherwise specified.

	Parameter	Max.	Units
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ⑥	5.2	A
$I_D @ T_A = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ⑤	3.8	
$I_D @ T_A = 70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$ ⑤	3.0	
I_{DM}	Pulsed Drain Current ①	30	W
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation (PCB Mount) ⑥	2.1	
$P_D @ T_A = 25^\circ\text{C}$	Power Dissipation (PCB Mount) ⑤	1.0	
	Linear Derating Factor (PCB Mount) ⑤	8.3	mW/°C
V_{GS}	Gate-to-Source Voltage	± 16	V
E_{AS}	Single Pulse Avalanche Energy (Thermally Limited) ②	110	mJ
I_{AR}	Avalanche Current ①	3.8	A
E_{AR}	Repetitive Avalanche Energy ①⑤	0.10	mJ
dv/dt	Peak Diode Recovery dv/dt ③	7.5	V/ns
T_J	Operating Junction and	-55 to + 150	°C
T_{STG}	Storage Temperature Range		

Thermal Resistance

	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Junction-to-Ambient (PCB mount, steady state) ③	93	120	°C/W
$R_{\theta JA}$	Junction-to-Ambient (PCB mount, steady state) ⑥	48	60	

HEXFET® is a registered trademark of International Rectifier.

*Qualification standards can be found at <http://www.irf.com/>

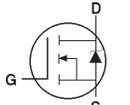
Static Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)DSS}	Drain-to-Source Breakdown Voltage	55	—	—	V	V _{GS} = 0V, I _D = 250μA
ΔV _{(BR)DSS} /ΔT _J	Breakdown Voltage Temp. Coefficient	—	0.061	—	V/°C	Reference to 25°C, I _D = 1mA
R _{DS(on)}	Static Drain-to-Source On-Resistance	—	—	0.040	Ω	V _{GS} = 10V, I _D = 3.8A ④
		—	—	0.051		V _{GS} = 5.0V, I _D = 3.8A ④
		—	—	0.065		V _{GS} = 4.0V, I _D = 1.9A ④
V _{GS(th)}	Gate Threshold Voltage	1.0	—	2.0	V	V _{DS} = V _{GS} , I _D = 250μA
g _{fs}	Forward Transconductance	5.1	—	—	S	V _{DS} = 25V, I _D = 1.9A
I _{DSS}	Drain-to-Source Leakage Current	—	—	25	μA	V _{DS} = 55V, V _{GS} = 0V
		—	—	250		V _{DS} = 44V, V _{GS} = 0V, T _J = 150°C
I _{GSS}	Gate-to-Source Forward Leakage	—	—	100	nA	V _{GS} = 16V
	Gate-to-Source Reverse Leakage	—	—	-100		V _{GS} = -16V

Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge	—	32	48	nC	I _D = 3.8A
Q _{gs}	Gate-to-Source Charge	—	3.5	5.3		V _{DS} = 44V
Q _{gd}	Gate-to-Drain ("Miller") Charge	—	9.7	14		V _{GS} = 10V, See Fig. 6 and 9 ④
t _{d(on)}	Turn-On Delay Time	—	6.2	—	ns	V _{DD} = 28V
t _r	Rise Time	—	12	—		I _D = 3.8A
t _{d(off)}	Turn-Off Delay Time	—	35	—		R _G = 6.2Ω
t _f	Fall Time	—	22	—		R _D = 7.1Ω, See Fig. 10 ④
C _{iss}	Input Capacitance	—	870	—	pF	V _{GS} = 0V
C _{oss}	Output Capacitance	—	220	—		V _{DS} = 25V
C _{rss}	Reverse Transfer Capacitance	—	92	—		f = 1.0MHz, See Fig. 5

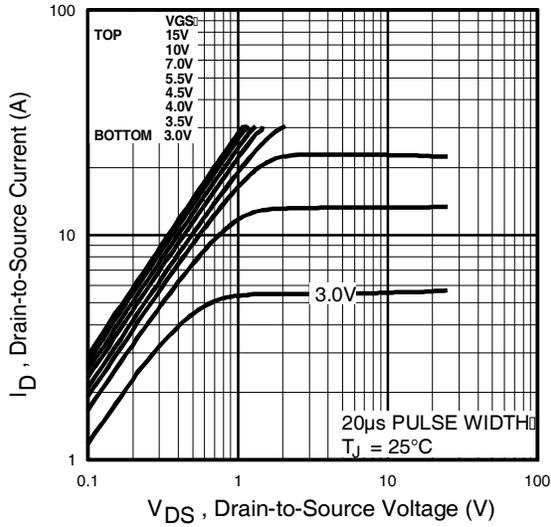
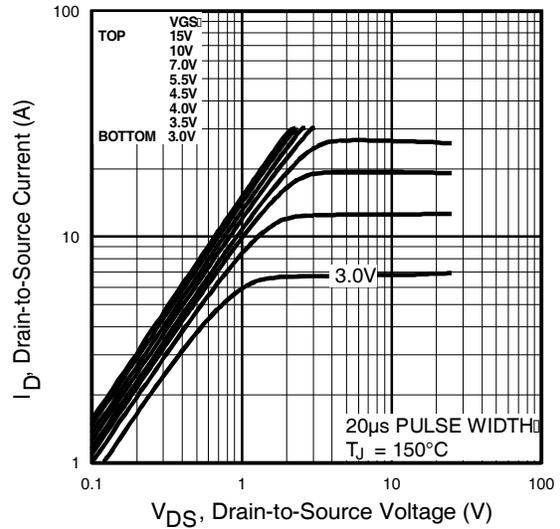
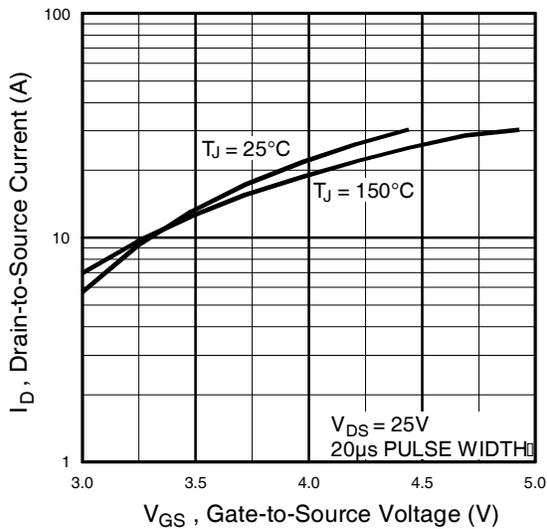
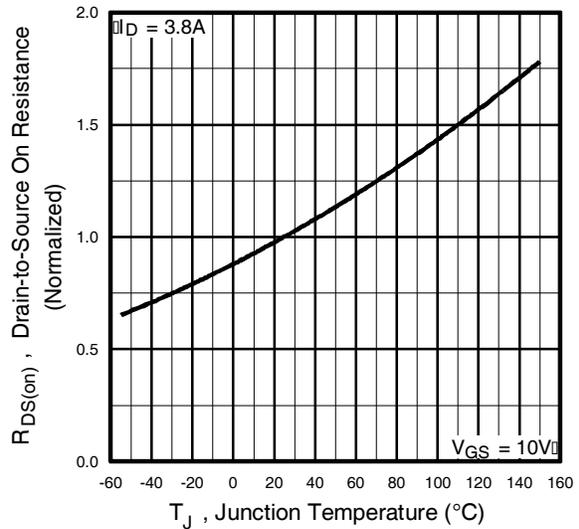
Diode Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I _S	Continuous Source Current (Body Diode)	—	—	0.91	A	MOSFET symbol showing the integral reverse p-n junction diode. 
I _{SM}	Pulsed Source Current (Body Diode) ①	—	—	30		
V _{SD}	Diode Forward Voltage	—	—	1.3	V	T _J = 25°C, I _S = 3.8A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	58	88	ns	T _J = 25°C, I _F = 3.8A
Q _{rr}	Reverse Recovery Charge	—	140	210	nC	di/dt = 100A/μs ④
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

- ① Repetitive rating; pulse width limited by max. junction temperature. (See fig. 11)
- ② V_{DD} = 25V, starting T_J = 25°C, L = 15mH
R_G = 25Ω, I_{AS} = 3.8A. (See Figure 12)
- ③ I_{SD} ≤ 3.8A, di/dt ≤ 220A/μs, V_{DD} ≤ V_{(BR)DSS},
T_J ≤ 150°C .

- ④ Pulse width ≤ 300μs; duty cycle ≤ 2%.
- ⑤ When mounted on FR-4 board using minimum recommended footprint.
- ⑥ When mounted on 1 inch square copper board, for comparison with other SMD devices.


Fig 1. Typical Output Characteristics

Fig 2. Typical Output Characteristics

Fig 3. Typical Transfer Characteristics

Fig 4. Normalized On-Resistance Vs. Temperature

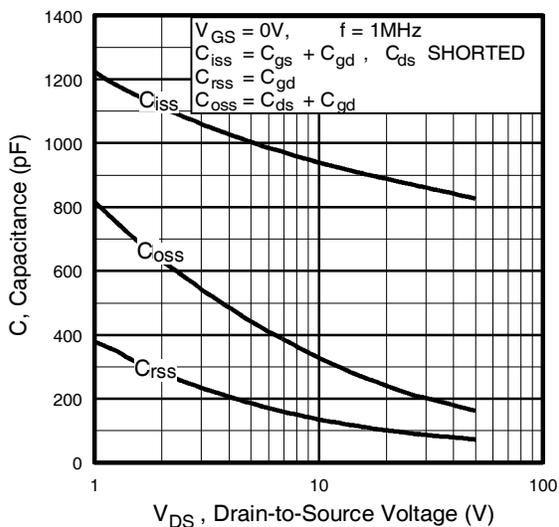


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

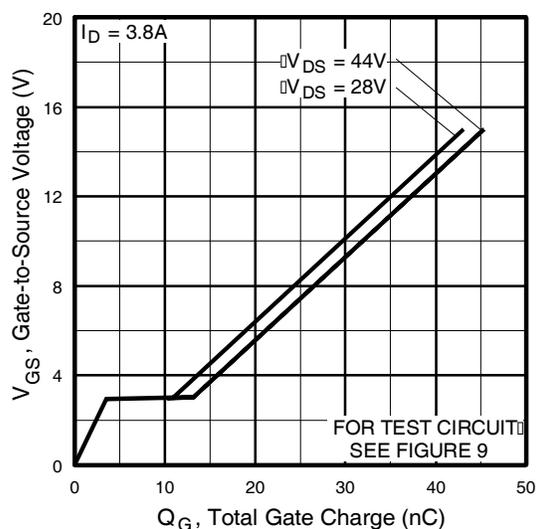


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

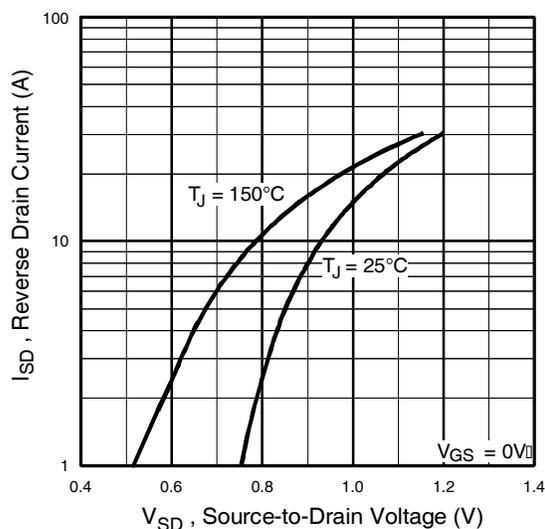


Fig 7. Typical Source-Drain Diode Forward Voltage

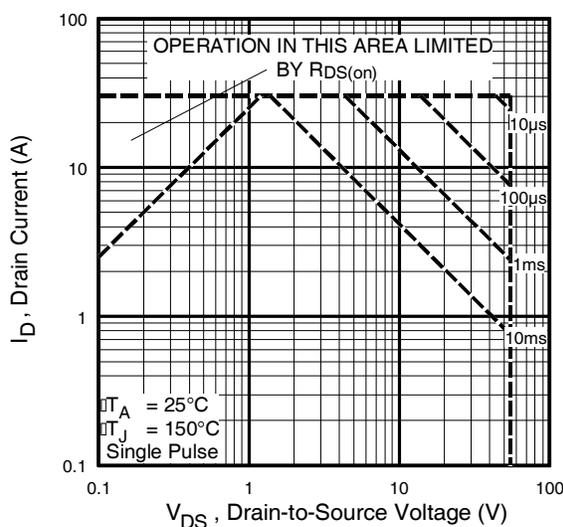
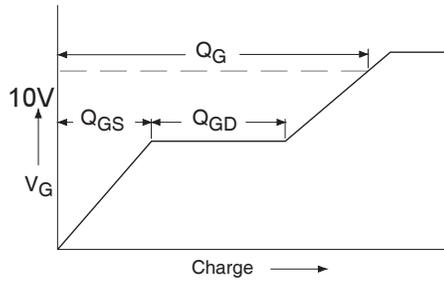
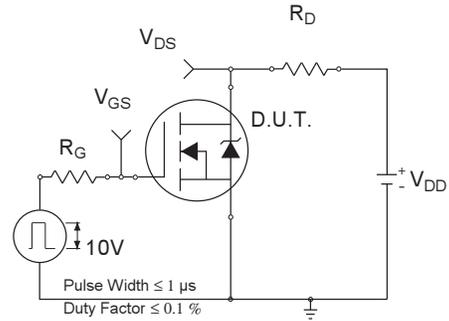
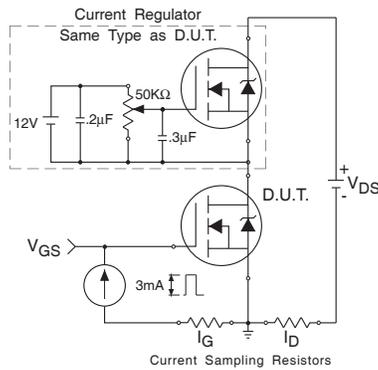
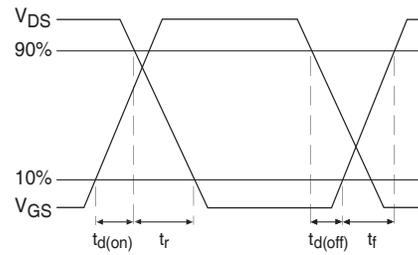
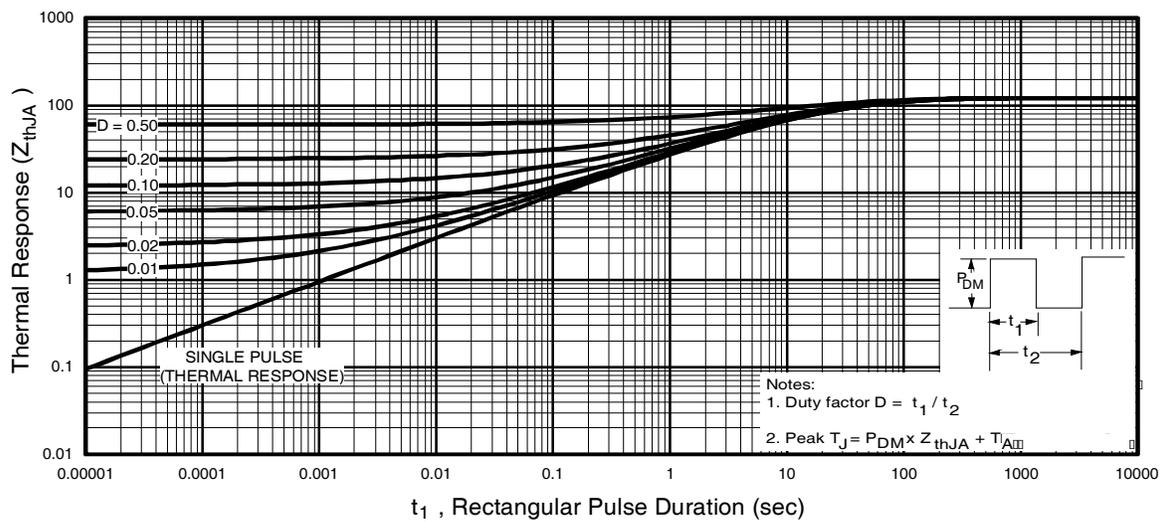
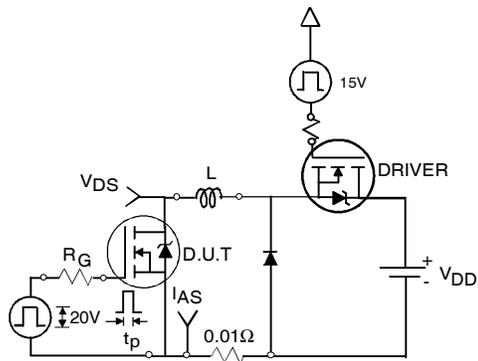
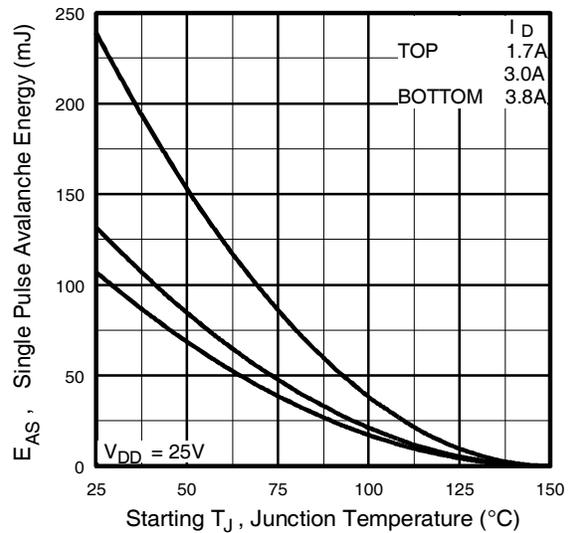
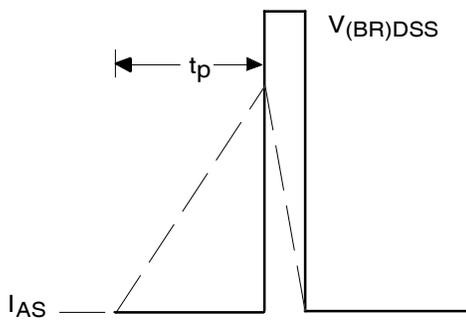
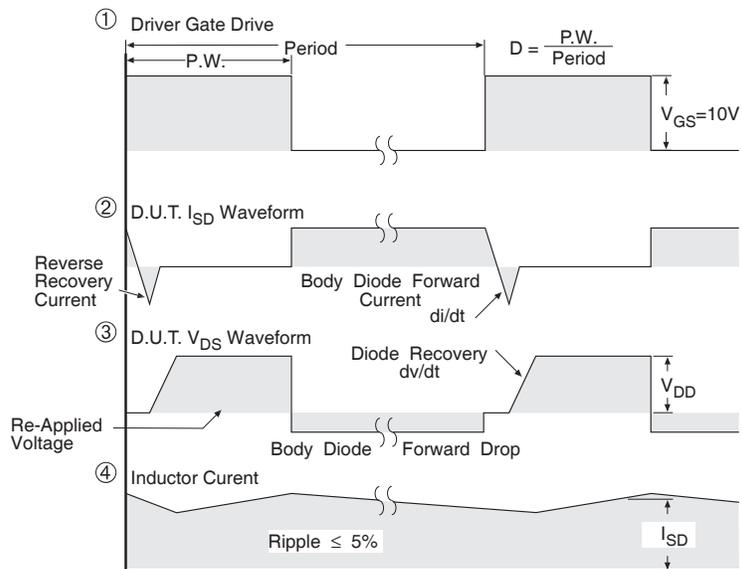
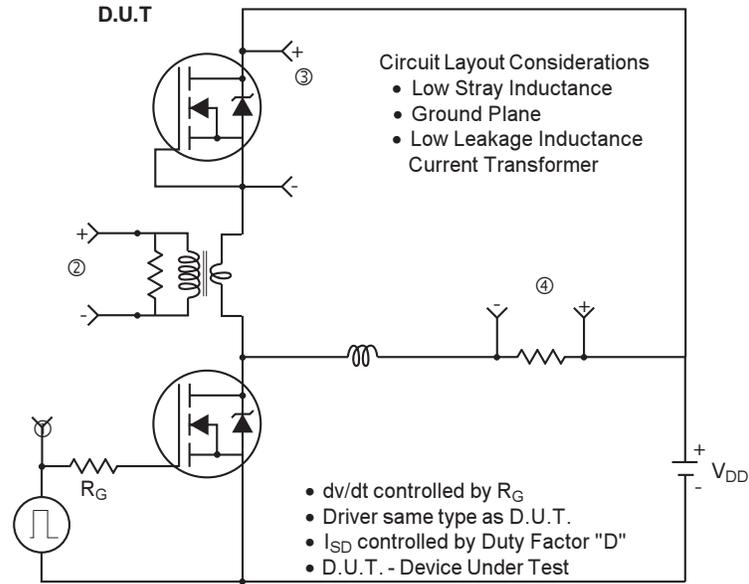


Fig 8. Maximum Safe Operating Area


Fig 9a. Basic Gate Charge Waveform

Fig 10a. Switching Time Test Circuit

Fig 9b. Gate Charge Test Circuit

Fig 10b. Switching Time Waveforms

Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Ambient


Fig 12a. Unclamped Inductive Test Circuit

Fig 12c. Maximum Avalanche Energy Vs. Drain Current

Fig 12b. Unclamped Inductive Waveforms

Peak Diode Recovery dv/dt Test Circuit

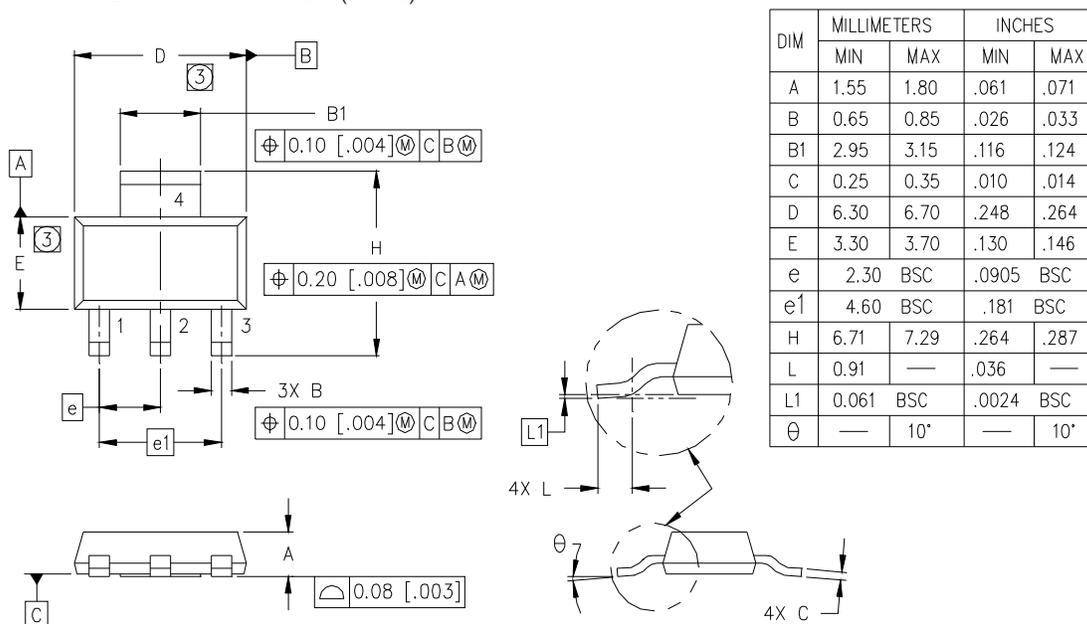


* $V_{GS} = 5V$ for Logic Level Devices

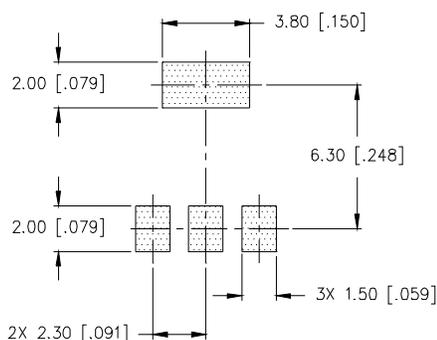
Fig 13. For N-Channel HEXFETS

SOT-223 (TO-261AA) Package Outline

Dimensions are shown in millimeters (inches)



MINIMUM RECOMMENDED FOOTPRINT



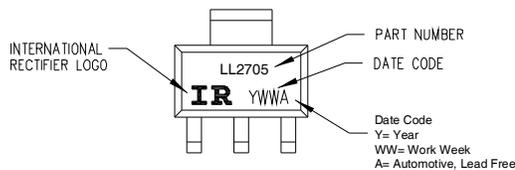
LEAD ASSIGNMENTS

- 1 = GATE
- 2 = DRAIN
- 3 = SOURCE
- 4 = DRAIN

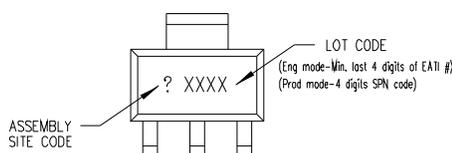
NOTES:

1. DIMENSIONING & TOLERANCING PER ASME Y14.5M-1994.
2. CONTROLLING DIMENSION: INCH.
- ③ DIMENSIONS DO NOT INCLUDE MOLD FLASH.
4. OUTLINE CONFORMS TO JEDEC OUTLINE TO-261AA.
5. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

SOT-223 (TO-261AA) Part Marking Information



TOP MARKING

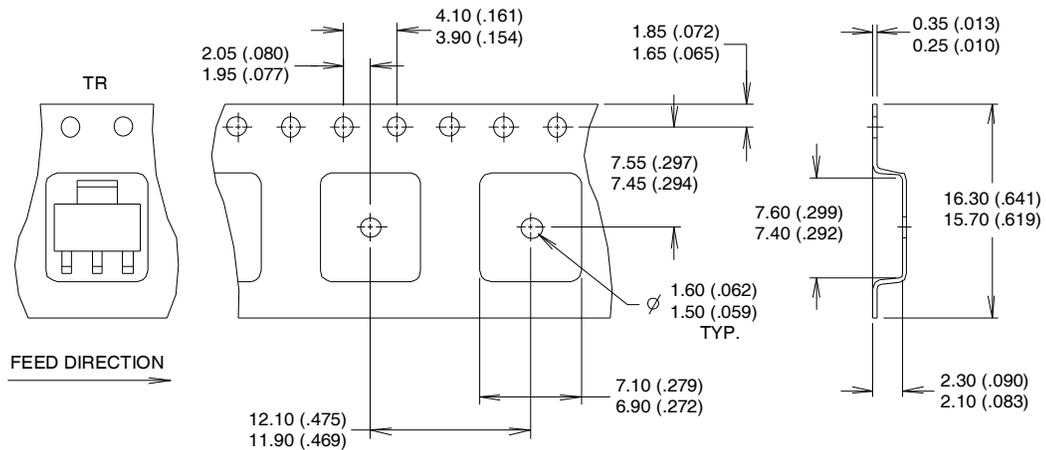


BOTTOM MARKING

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

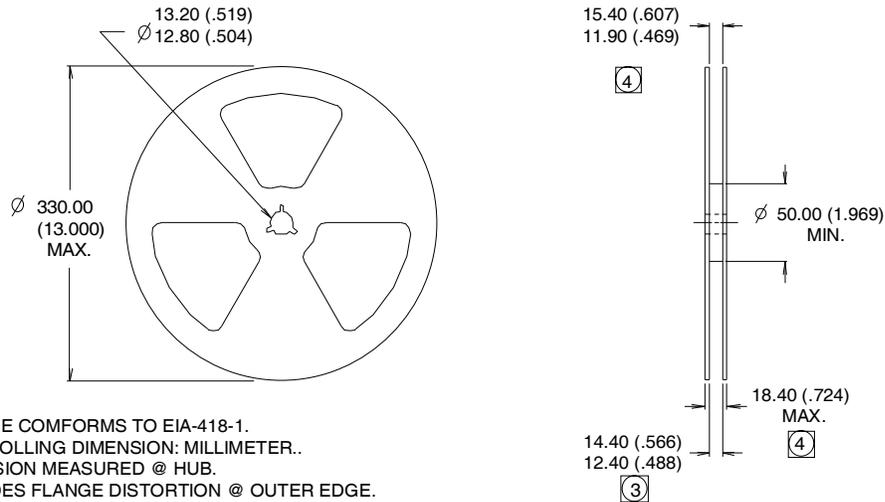
SOT-223 (TO-261AA) Tape & Reel Information

Dimensions are shown in millimeters (inches)



NOTES :

1. CONTROLLING DIMENSION: MILLIMETER.
2. OUTLINE CONFORMS TO EIA-481 & EIA-541.
3. EACH $\varnothing 330.00$ (13.00) REEL CONTAINS 2,500 DEVICES.



NOTES :

1. OUTLINE CONFORMS TO EIA-418-1.
2. CONTROLLING DIMENSION: MILLIMETER..
- ③ DIMENSION MEASURED @ HUB.
- ④ INCLUDES FLANGE DISTORTION @ OUTER EDGE.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level		Automotive (per AEC-Q101) ^{††}	
		Comments: This part number(s) passed Automotive qualification. IR's Industrial and Consumer qualification level is granted by extension of the higher Automotive level.	
Moisture Sensitivity Level		SOT-223	MSL1
ESD	Machine Model	Class M2 (+/- 200V) ^{†††} AEC-Q101-002	
	Human Body Model	Class H1B (+/- 750V) ^{†††} AEC-Q101-001	
	Charged Device Model	Class C5 (+/- 1125V) ^{†††} AEC-Q101-005	
RoHS Compliant		Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/>

†† Exceptions (if any) to AEC-Q101 requirements are noted in the qualification report.

††† Highest passing voltage.

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<http://www.irf.com/technical-info/>

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 Tel: (310) 252-7105

Revision History

Date	Comments
3/26/2014	<ul style="list-style-type: none"> • Added "Logic Level Gate Drive" bullet in the features section on page 1 • Updated part marking on page 8 • Updated data sheet with new IR corporate template

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